To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SC2545, 2SC2546, 2SC2547

Silicon NPN Epitaxial

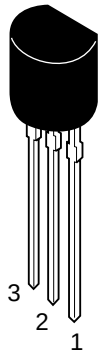
ADE-208-1067A (Z)
2nd. Edition
Mar. 2001

Application

- Low frequency low noise amplifier

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SC2545	2SC2546	2SC2547	Unit
Collector to base voltage	V_{CBO}	60	90	120	V
Collector to emitter voltage	V_{CEO}	60	90	120	V
Emitter to base voltage	V_{EBO}	5	5	5	V
Collector current	I_C	100	100	100	mA
Emitter current	I_E	–100	–100	–100	mA
Collector power dissipation	P_C	400	400	400	mW
Junction temperature	Tj	150	150	150	°C
Storage temperature	Tstg	–55 to +150	–55 to +150	–55 to +150	°C

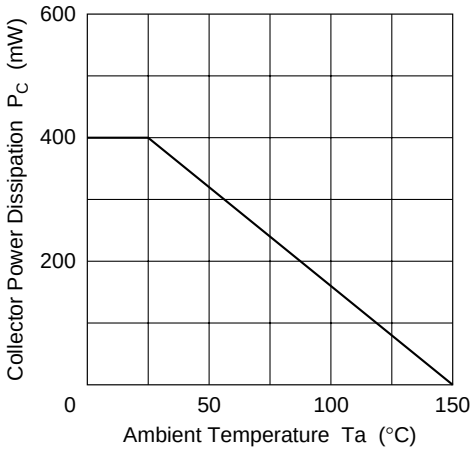
Electrical Characteristics (Ta = 25°C)

		2SC2545			2SC2546			2SC2547				
Item	**Symbol**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Unit**	**Test conditions**
Collector to base breakdown voltage	$V_{(BR)CBO}$	60	—	—	90	—	—	120	—	—	V	I_C = 10 µA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	60	—	—	90	—	—	120	—	—	V	I_C = 1 mA, R_{BE} =
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	5	—	—	5	—	—	V	I_E = 10 µA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	0.1	—	—	0.1	—	—	0.1	µA	V_{CB} = 50 V, I_E = 0
Emitter cutoff current	I_{EBO}	—	—	0.1	—	—	0.1	—	—	0.1	µA	V_{EB} = 2 V, I_C = 0
DC current transfer ratio	h_{FE}*[1]	250	—	1200	250	—	1200	250	—	800		V_{CE} = 12 V, I_C = 2 mA
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.2	—	—	0.2	—	—	0.2	V	I_C = 10 mA, I_B = 1 mA
Base to emitter voltage	V_{BE}	—	0.6	—	—	0.6	—	—	0.6	—	V	V_{CE} = 12 V, I_C = 2 mA
Gain bandwidth product	f_T	—	90	—	—	90	—	—	90	—	MHz	V_{CE} = 12 V, I_C = 2 mA
Collector output capacitance	Cob	—	3.0	—	—	3.0	—	—	3.0	—	pF	V_{CB} = 10 V, I_E = 0, f = 1 MHz
Noise voltage referred input	e_n	—	0.5	—	—	0.5	—	—	0.5	—	nV/$\sqrt{Hz}$	V_{CE} = 6V, I_C = 10 mA, f = 1 kHz, R_g = 0, Δf = 1Hz

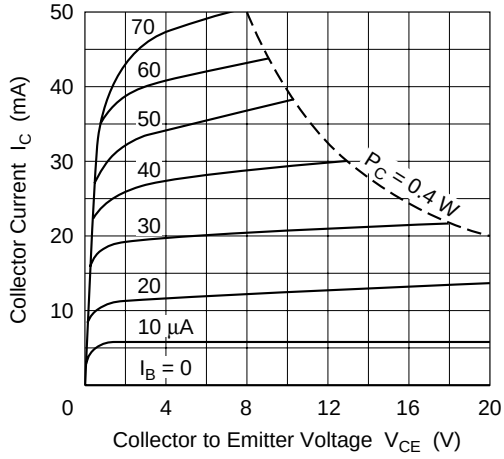
Note: 1. The 2SC2545, 2SC2546 and 2SC2547 are grouped by h_{FE} as follows.

	D	**E**	**F**
2SC2545, 2SC2546	250 to 500	400 to 800	600 to 1200
2SC2547	250 to 500	400 to 800	—

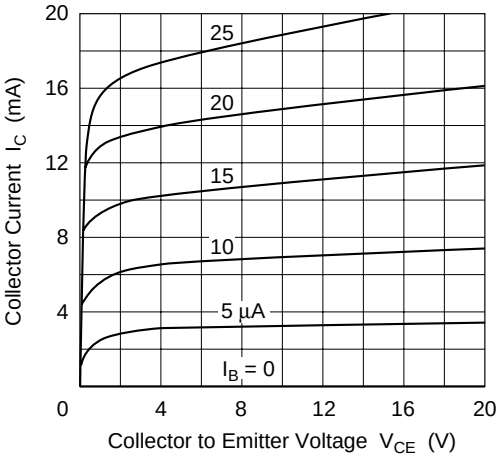
Maximum Collector Dissipation Curve



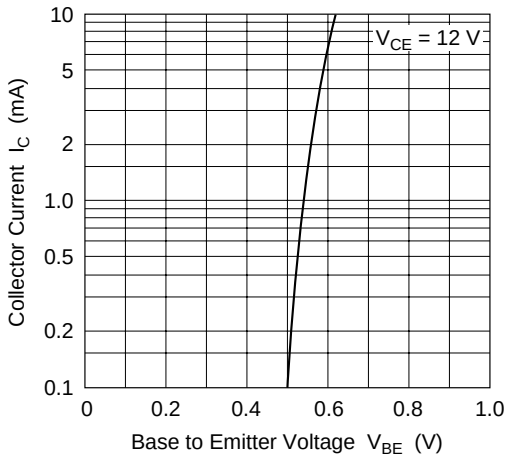
Typical Output Characteristics



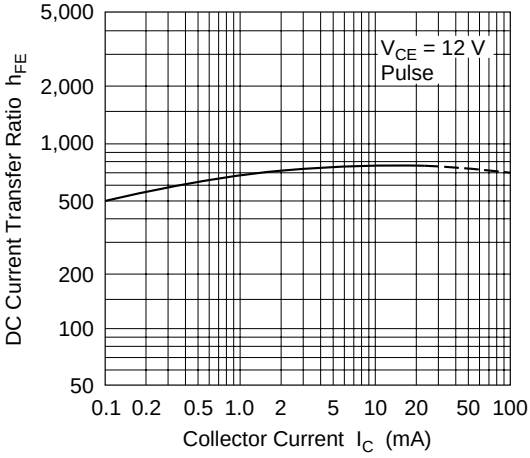
Typical Output Characteristics



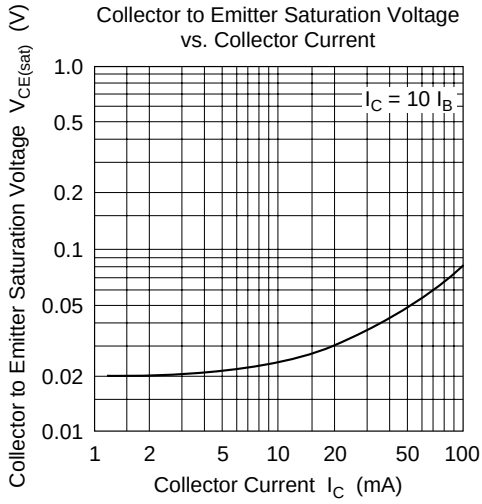
Typical Transfer Characteristics



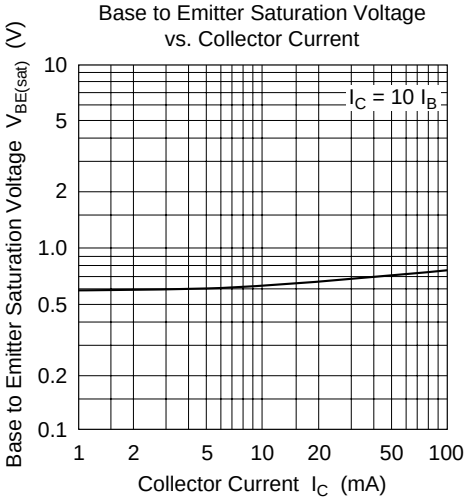
DC Current Transfer Ratio vs. Collector Current



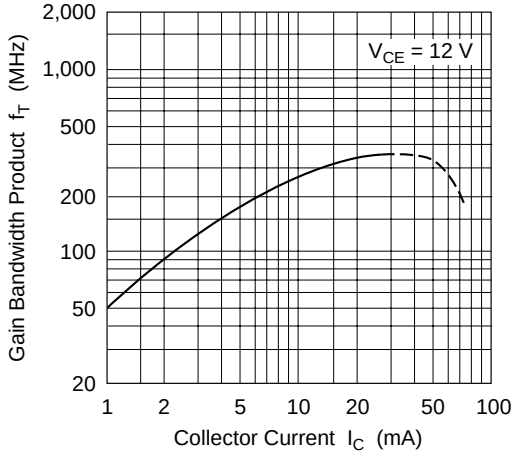
Collector to Emitter Saturation Voltage vs. Collector Current



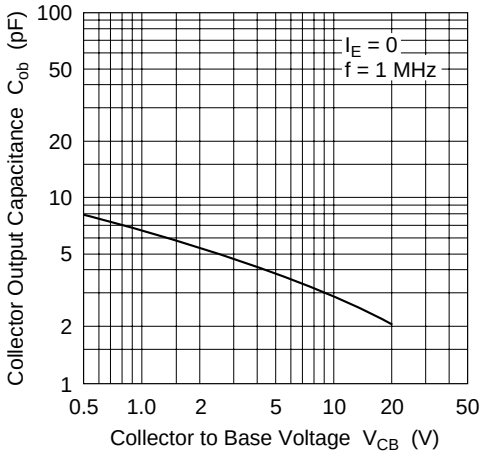
Base to Emitter Saturation Voltage vs. Collector Current



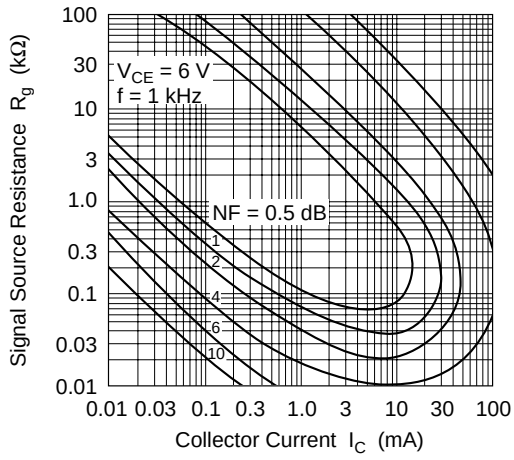
Gain Bandwidth Product vs. Collector Current



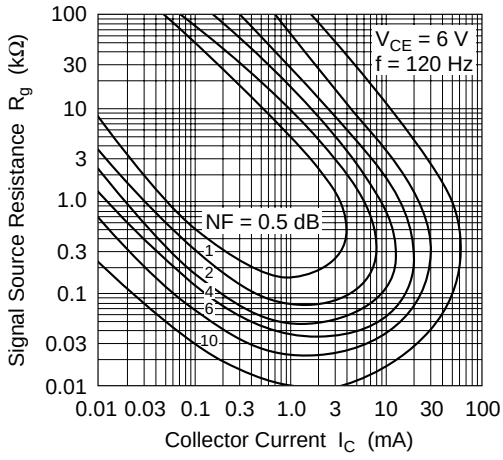
Collector Output Capacitance vs. Collector to Base Voltage



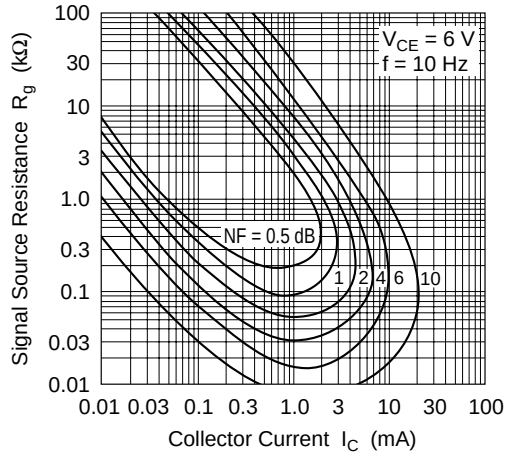
Contours of Constant Noise Figure



Contours of Constant Noise Figure



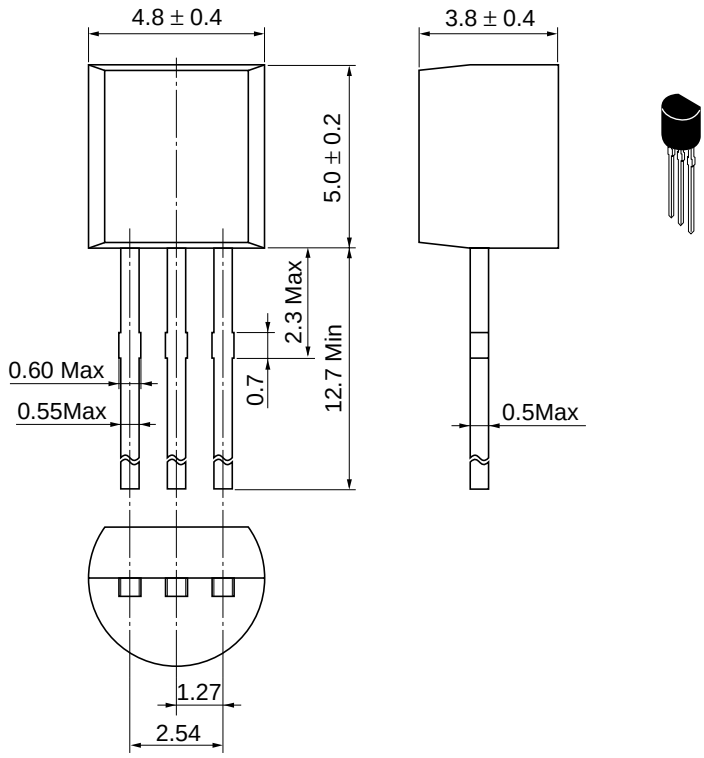
Contours of Constant Noise Figure



Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

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Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : http://semiconductor.hitachi.com/
Europe : http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor (America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straβe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : http://www.hitachi.com.sg

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
Fax : <852>-(2)-730-0281
URL : http://www.hitachi.com.hk

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